1751-294 GFR:daw APR 3 0 2000 TO

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IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re Application of)
Chan-ho PARK)
Serial No. 10/024475) Examiner: Junghwa M. IM
Filed: December 21, 2001) Group Art Unit: 2811

For: HIGH VOLTAGE SEMICONDUCTOR DEVICE HAVING HIGH BREAKDOWN

VOLTAGE AND METHOD OF FABRICATING THE SAME

INFORMATION DISCLOSURE STATEMENT

Assistant Commissioner for Patents Washington, D.C. 20231

Dear Sir:

Under the provisions of 37 C.F.R. §§ 1.56, 1.97 and 1.98,

Applicant submits herewith copies of publications that the Office may wish to consider in examination of the subject application.

The publications are listed on the attached form PTO-1449.

The relevance of any foreign-language reference for which an English-language translation is not provided is as follows.

JP 4-323832 has been cited in an Office Action issued by the Korean Patent Office during examination of the corresponding Korean application.

I hereby certify that each item of information contained in this information disclosure statement was first cited in a

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communication from a foreign patent office in a counterpart foreign application not more than three months prior to the filing of this statement.

Respectfully submitted,

Ву

G. Franklin Rothwell Attorney for Applicants Registration No. 18,125

ROTHWELL, FIGG, ERNST & MANBECK, p.c.

Suite 800, 1425 K Street, N.W.

Washington, D.C. 20005 Telephone: (202)783-6040

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INFORMATION DECLOSURE STATEMENT BY APPLICANT		Applic	Application Number 10/024475								
			Filing Date			December 21, 2001					
		First Named Inventor			Chan-ho PARK						
			Group Art Unit		2811						
			Examiner Name		Junghwa M. IM						
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				U	J.S. PA	TENT	DOCUMENTS				}
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	1	JP 4-323832 (abstract attact			ed)		MITSUBISHI ELECTRIC CORP		RP 11	11/13/1992	
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Examiner Signature								Date Considered			

^{*}EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

¹Unique citation designation number. ²See attached Kinds of U.S. Patent Documents. ³Enter Office that issued the document, by the two-letter code. ⁴For Japanese patent documents, the indication of the year of the reign of the Emperor must precede the serial number of the patent document. ⁵Kind of document by the appropriate symbols as indicated on the document under WIPO Standard ST. 16 if possible. ⁶Applicant is to place a check mark here if English language translation is attached. AB indicates that only an English language abstract is attached.